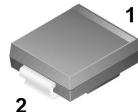
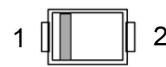



Features:

- Metal silicon junction, majority carrier conduction
- For surface mounted applications
- Low power loss, high efficiency
- Fast switching for high efficiency
- High forward surge current capability
- For use in low voltage, high frequency inverters

 DO-214AB
 (SMC)


2



1.Cathode 2. Anode

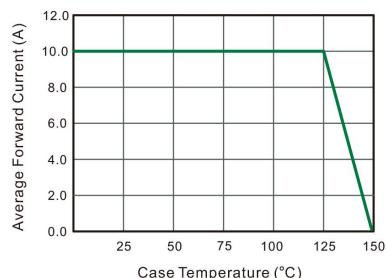
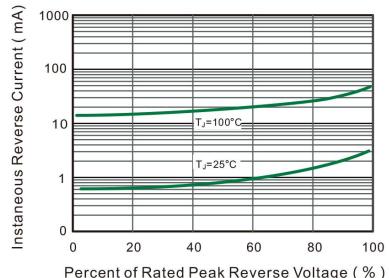
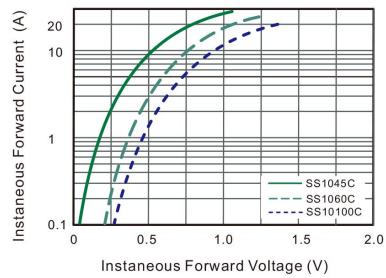
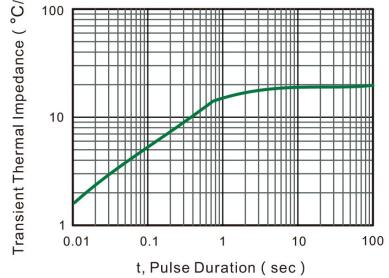
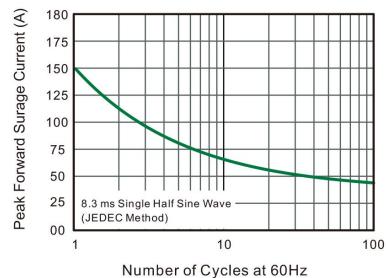
Absolute Maximum Ratings* (TA=25°C Unless otherwise noted)

Ratings at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz resistive or inductive load, for capacitive load, derate by 20 %

Parameter	Symbols	CH1045C	CH1060C	CH10100C	Units
Maximum Repetitive Peak Reverse Voltage	V _{RRM}	45	60	100	V
Maximum RMS voltage	V _{RMS}	32	42	70	V
Maximum DC Blocking Voltage	V _{DC}	45	60	100	V
Maximum Average Forward Rectified Current	I _{F(AV)}		10.0		A
Peak Forward Surge Current, 8.3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I _{FSM}		150		A
Max Instantaneous Forward Voltage @10.0 A	V _F	0.55	0.75	0.90	V
Maximum DC Reverse Current T _j = 25°C at Rated DC Reverse Voltage T _j = 100°C	I _R		0.5 50		mA
Typical Thermal Resistance	R _{θJA}		20		°C/W
Operating Junction Temperature Range	T _j		-55 ~ +150		°C
Storage Temperature Range	T _{stg}		-55 ~ +150		°C

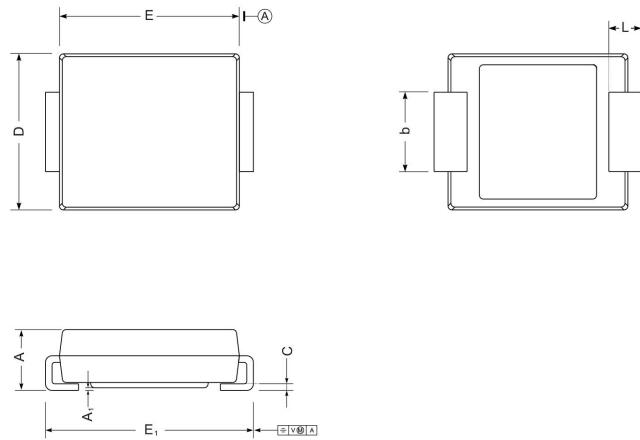
(1) P.C.B. mounted with 2.0" X 2.0" (5 X 5 cm) copper pad areas.

Typical Characteristics

Fig.1 Forward Current Derating Curve

Fig.2 Typical Reverse Characteristics

Fig.3 Typical Forward Characteristic

Fig.4- Typical Transient Thermal Impedance

Fig.5 Maximum Non-Repetitive Peak Forward Surge Current


Package Dimension

DO-214AB (SMC)



SMC mechanical data

UNIT		A	E	D	E ₁	A ₁	C	L	b
mm	max	2.62	7.0	6.2	8.0	0.21	0.31	1.6	3.25
	min	2.00	6.5	5.6	7.6	0.05	0.15	0.9	2.75
mil	max	103	276	244	315	8.3	12	63	128
	min	79	256	220	299	2.0	5.9	35	108

The recommended mounting pad size

